SKN 2F17



Stud Diode

Fast Recovery Rectifier Diode

SKN 2F17 SKR 2F17

Features

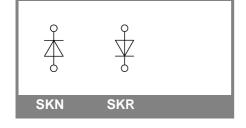
- · Small recovered charge
- Soft recovery
- Up to 1000 V reverse voltage
- Hermetic metal case with glass insulator
- Threaded stud ISO M5 or 10-32 UNF
- SKN: anode to stud SKR: cathode to stud

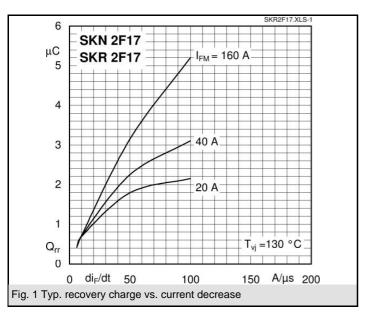
Typical Applications

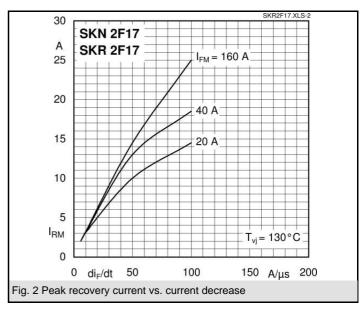
- Inverse diode for power transistor, GTO thyristor, asymmetric thyristor
- SMPS, inverters, choppers
- for severe ambient conditions

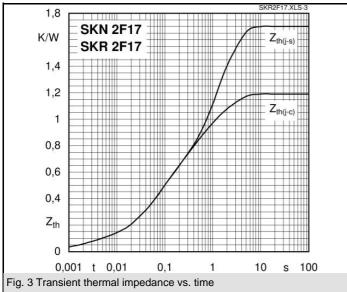
| V _{RSM} | V_{RRM} | I _{FRMS} = 41 A (maximum value for continuous operation) | | |
|------------------|-----------|---|----------------|--|
| V | V | I _{FAV} = 17 A (sin. 180; 5000Hz; T _c = 113 °C) | | |
| 400 | 400 | SKN 2F17/04 | SKR 2F17/04 | |
| 400 | 400 | SKN 2F17/04UNF | SKR 2F17/04UNF | |
| 600 | 600 | SKN 2F17/06 | SKR 2F17/06 | |
| 600 | 600 | SKN 2F17/06UNF | SKR 2F17/06UNF | |
| 800 | 800 | SKN 2F17/08 | SKR 2F17/08 | |
| 800 | 800 | SKN 2F17/08UNF | SKR 2F17/08UNF | |
| 1000 | 1000 | SKN 2F17/10 | SKR 2F17/10 | |
| 1000 | 1000 | SKN 2F17/10UNF | SKR 2F17/10UNF | |

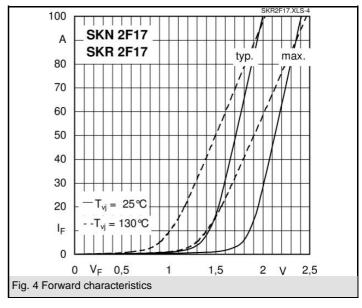
| Symbol | Conditions | Values | Units |
|----------------------|--|-------------------|-------|
| I _{FAV} | sin. 180; T _c = 85 (100) °C | 26 (22) | Α |
| I_{FAV} | K5,5; T _a = 45 °C; sin. 180; 5000 Hz | 10 | Α |
| I _{FSM} | T _{vi} = 25 °C; 10 ms | 450 | А |
| | T _{vi} = 150 °C; 10 ms | 380 | Α |
| i²t | T _{vi} = 25 °C; 8,3 10 ms | 1000 | A²s |
| | T _{vj} = 150 °C; 8,3 10 ms | 720 | A²s |
| V _F | T _{vi} = 25 °C; I _F = 50 A | max. 2,15 | V |
| $V_{(TO)}$ | T _{vi} = 130 °C | max. 1,3 | V |
| r _T | $T_{vj} = 130 ^{\circ}\text{C}$ | max. 12 | mΩ |
| I_{RD} | $T_{vj} = 25 ^{\circ}C; V_{RD} = V_{RRM}$ | max. 0,2 | mA |
| I_{RD} | T_{vj} = 130 °C, V_{RD} = V_{RRM} | max. 16 | mA |
| Q _{rr} | T _{vi} = 130 °C, I _F = 50 A, | 1 | μC |
| I _{RM} | -di/dt = 15 A/μs, V _R = 30 V | 4,5 | Α |
| t _{rr} | | 440 | ns |
| E _{rr} | | - | mJ |
| R _{th(j-c)} | | 1,2 | K/W |
| R _{th(c-s)} | | 0,5 | K/W |
| T _{vj} | | - 40 + 150 | °C |
| T _{stg} | | - 55 + 150 | °C |
| V _{isol} | | - | V~ |
| M_s | to heatsink | 1,5 | Nm |
| а | | 5 * 9,81 | m/s² |
| m | approx. | 7 | g |
| Case | | E7 | |
| | | | |
| | | | |

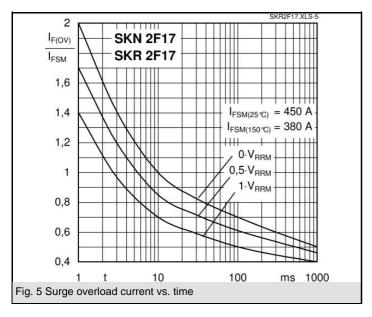


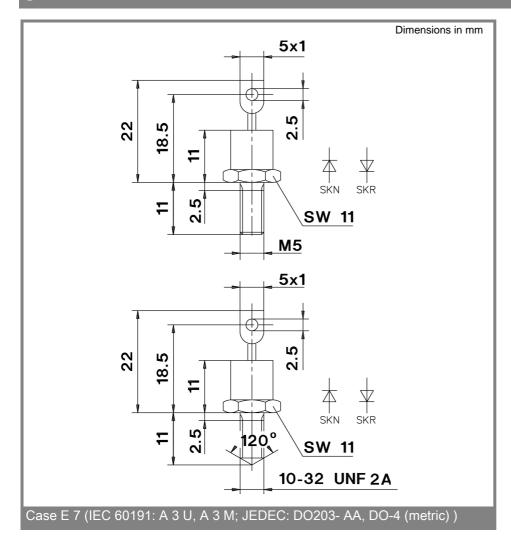












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